

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L6	2374	438/3.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/04 13:22
S49	2380	257/295.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/04 13:21
S42	5499	(@ad<"20020820" or @rlad<"20020820") and ((ferroelectric adj memory) or FRAM or (ferroelectric adj device)) and (substrate ferroelectric layer barrier transistor gate drain source electrode conductor schottky FET (field adj effect adj transistor) MOSFET chalcogenide "Ag" "Pt" "Cu" "Zn.sub.xCd.sub.1-xS" "Cu.sub.2S") not S41	US-PGPUB; USPAT; USOCR; IBM_TDB	OR	ON	2007/09/04 12:36
L5	129	"5512773"	US-PGPUB; USPAT; USOCR; IBM_TDB	OR	ON	2007/09/04 12:36
L4	4	(ferroelectric and oxygen and substrate and schottky).clm.	US-PGPUB; USPAT; USOCR	OR	ON	2007/09/04 12:17
L3	3	(ferroelectric and gate and (drain source) and barrier and substrate and schottky).clm.	US-PGPUB; USPAT; USOCR	OR	ON	2007/09/04 12:17
S51	304	(ferroelectric and gate and (drain source) and barrier and substrate and schottky)	US-PGPUB; USPAT; USOCR	OR	ON	2007/09/04 12:15
S48	1414	(@ad<"20020820" or @rlad<"20020820") and 257/295.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/04 09:01

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S47	446	(@ad<"20020820" or @rlad<"20020820") and 257/E21.663-E21.664.ccls. and ((ferroelectric adj memory) or FRAM or (ferroelectric adj device)) and (substrate ferroelectric layer barrier transistor gate drain source electrode conductor schottky FET (field adj effect adj transistor) MOSFET chalcogenide "Ag" "Pt" "Cu"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/04 09:01
S46	2073	257/E43.001-E43.007.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/04 08:12
S45	47	(@ad<"20020820" or @rlad<"20020820") and 438/86.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/31 15:19
S44	47	("4888630" "5046043" "5229309" "5300799" "5303182" "5416735" "5440173" "5495117" "5498888" "5559733").PN. OR ("5708284").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/08/31 14:55
S43	2332	(@ad<"20020820" or @rlad<"20020820") and ((ferroelectric adj memory) or FRAM or (ferroelectric adj device)) and substrate and ferroelectric and transistor and (barrier gate drain source electrode conductor schottky FET (field adj effect adj transistor) MOSFET chalcogenide "Ag" "Pt" "Cu" "Zn.sub.xCd.sub.1-xS" "Cu.sub.2S") not S41	US-PGPUB; USPAT; USOCR; IBM_TDB	OR	ON	2007/08/31 12:38
S41	539	(@ad<"20020820" or @rlad<"20020820") and ((ferroelectric adj memory) or FRAM or (ferroelectric adj device)) and FRAM.ab. and (substrate ferroelectric layer barrier transistor gate drain source electrode conductor schottky FET (field adj effect adj transistor) MOSFET chalcogenide "Ag" "Pt" "Cu" "Zn.sub.xCd.sub.1-xS" "Cu.sub.2S"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/31 12:32

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S13	813	(@ad<"20020820" or @rlad<"20020820") and ((ferroelectric adj memory) or FRAM or (ferroelectric adj device)) and FRAM.ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/31 10:32
S40	906	(@ad<"20020820" or @rlad<"20020820") and 438/95. ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 09:03
S38	29	(@ad<"20020820" or @rlad<"20020820") and 438/84. ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 09:03
S37	141	(@ad<"20020820" or @rlad<"20020820") and ("5600587" "5572459" "5550770" "5530668" "5541872") and ((ferroelectric adj memory) FRAM ferroelectric (ferroelectric adj device) schottky FET (field adj effect adj transistor) MOSFET chalcogenide "Ag" "Pt" "Cu" Mg\$5F.sub\$3 "Zn.sub.xCd.sub.1-xS" "Cu.sub.2S")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/23 09:02
S26	0	"5146229" and ((ferroelectric adj memory) FRAM (ferroelectric adj device) schottky FET (field adj effect adj transistor) MOSFET chalcogenide "Ag" "Pt" "Cu" "Zn. sub.xCd.sub.1-xS" "Cu.sub.2S")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/20 13:15
S36	45	(@ad<"20020820" or @rlad<"20020820") and "5303182" and ((ferroelectric adj memory) FRAM (ferroelectric adj device) schottky FET (field adj effect adj transistor) MOSFET chalcogenide "Ag" "Pt" "Cu" "Zn.sub.xCd.sub.1-xS" "Cu.sub.2S")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/20 12:11
S29	85	(@ad<"20020820" or @rlad<"20020820") and "5146299" and ((ferroelectric adj memory) FRAM (ferroelectric adj device) schottky FET (field adj effect adj transistor) MOSFET chalcogenide "Ag" "Pt" "Cu" "Zn.sub.xCd.sub.1-xS" "Cu.sub.2S")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/20 11:59

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S35	54	"5303182"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/18 15:50
S34	112	(@ad<"20020820" or @rlad<"20020820") and semiconductor and ("257" "438" "365").clas. and (BaMF\$ BaMgF\$ BaMnF\$ BaZnF\$ BaFeF\$ BaCoF\$ BaNiF\$) and ((ferroelectric adj memory) FRAM silicon semiconductor substrate (ferroelectric adj device) schottky FET (field adj effect adj transistor) MOSFET chalcogenide "Ag" "Pt" "Cu" "Zn.sub.xCd.sub.1-xS" "Cu.sub. 2S")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/18 15:50
S33	820	(@ad<"20020820" or @rlad<"20020820") and (BaMF\$ BaMgF\$ BaMnF\$ BaZnF\$ BaFeF\$ BaCoF\$ BaNiF\$) and ((ferroelectric adj memory) FRAM silicon semiconductor substrate (ferroelectric adj device) schottky FET (field adj effect adj transistor) MOSFET chalcogenide "Ag" "Pt" "Cu" "Zn.sub.xCd.sub.1-xS" "Cu.sub. 2S")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/18 14:19
S32	30	(@ad<"20020820" or @rlad<"20020820") and (BaMF BaMgF BaMnF BaZnF BaFeF BaCoF BaNiF) and ((ferroelectric adj memory) FRAM silicon semiconductor substrate (ferroelectric adj device) schottky FET (field adj effect adj transistor) MOSFET chalcogenide "Ag" "Pt" "Cu" "Zn.sub.xCd.sub.1-xS" "Cu.sub. 2S")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/18 14:17
S31	1	(@ad<"20020820" or @rlad<"20020820") and ferroelectric and (BaMF BaMgF BaMnF BaZnF BaFeF BaCoF BaNiF) and ((ferroelectric adj memory) FRAM (ferroelectric adj device) schottky FET (field adj effect adj transistor) MOSFET chalcogenide "Ag" "Pt" "Cu" "Zn.sub.xCd.sub. 1-xS" "Cu.sub.2S")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/18 14:09

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S30	0	(@ad<"20020820" or @rlad<"20020820") and 365/171. ccls. and ferroelectric and (BaMF BaMgF BaMnF BaZnF BaFeF BaCoF BaNiF) and ((ferroelectric adj memory) FRAM (ferroelectric adj device) schottky FET (field adj effect adj transistor) MOSFET chalcogenide "Ag" "Pt" "Cu" "Zn. sub.xCd.sub.1-xS" "Cu.sub.2S")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/18 14:02
S24	377	(@ad<"20020820" or @rlad<"20020820") and 365/171. ccls. and ((ferroelectric adj memory) FRAM (ferroelectric adj device) schottky FET (field adj effect adj transistor) MOSFET chalcogenide "Ag" "Pt" "Cu" "Zn.sub.xCd.sub.1-xS" "Cu.sub.2S")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/18 13:55
S28	92	"5146299" and ((ferroelectric adj memory) FRAM (ferroelectric adj device) schottky FET (field adj effect adj transistor) MOSFET chalcogenide "Ag" "Pt" "Cu" "Zn. sub.xCd.sub.1-xS" "Cu.sub.2S")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/18 11:46
S27	4	"5146229"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/18 11:05
S25	303	(@ad<"20020820" or @rlad<"20020820") and 257/43,76. ccls. and ((ferroelectric adj memory) FRAM (ferroelectric adj device) schottky FET (field adj effect adj transistor) MOSFET chalcogenide "Ag" "Pt" "Cu" "Zn.sub.xCd.sub.1-xS" "Cu.sub.2S")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/18 11:05
S3	0	(@ad<"20020820" or @rlad<"20020820") and ((ferroelectric adj memory) or FRAM or (ferroelectric adj device)) and schottky and (FET or (field adj effect adj transistor) or MOSFET) and chalcogenide and "Ag" and "Pt" and "Cu" and "Zn.sub.xCd.sub.1-xS" and "Cu.sub.2S"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/18 10:08

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S23	14	257/E43.001-E43.007.ccls. and ferroelectric and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/16 15:29
S21	14	257/E43.001.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/16 15:28
S16	11	(@ad<"20020820" or @rlad<"20020820") and 438/3.ccls. and (Ag or Au or Cd or ferroelectric or layer or Cu or schottky or oxygen or memory) and "Cu.sub.2S"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/16 15:22
S19	5	oxygen near2 free near2 ferroelectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/23 09:11
S18	4	oxygen adj free adj ferroelectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/23 09:11
S17	62	(@ad<"20020820" or @rlad<"20020820") and (ferroelectric or FRAM or (ferroelectric adj device)) and (FET or (field adj effect adj transistor) or MOSFET or transistor) and chalcogenide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/22 13:39
S11	9173	(@ad<"20020820" or @rlad<"20020820") and ((ferroelectric adj memory) or FRAM or (ferroelectric adj device))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/22 13:36
S8	0	(@ad<"20020820" or @rlad<"20020820") and ((ferroelectric adj memory) or FRAM or (ferroelectric adj device)) and "Ag" and "Pt" and "Cu" and "Zn.sub.xCd.sub.1-xS" and "Cu.sub.2S"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/22 13:36

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S15	1366	(@ad<"20020820" or @rlad<"20020820") and 438/3.ccls. and (Ag or Au or Cd or ferroelectric or layer or Cu or schottky or oxygen or memory or "Cu.sub."\$)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/22 13:21
S14	1366	(@ad<"20020820" or @rlad<"20020820") and 438/3.ccls. and (Ag or Au or Cd or ferroelectric or layer or Cu or schottky or oxygen or memory)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/22 13:17
S10	212	(@ad<"20020820" or @rlad<"20020820") and ((ferroelectric adj memory) or FRAM or (ferroelectric adj device)) and "Ag" and "Pt" and "Cu"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/22 13:05
S7	0	(@ad<"20020820" or @rlad<"20020820") and ((ferroelectric adj memory) or FRAM or (ferroelectric adj device)) and (FET or (field adj effect adj transistor) or MOSFET) and "Ag" and "Pt" and "Cu" and "Zn.sub.xCd.sub.1-xS" and "Cu.sub.2S"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/22 12:37
S6	0	(@ad<"20020820" or @rlad<"20020820") and ((ferroelectric adj memory) or FRAM or (ferroelectric adj device)) and (FET or (field adj effect adj transistor) or MOSFET) and chalcogenide and "Ag" and "Pt" and "Cu" and "Zn.sub.xCd.sub.1-xS" and "Cu.sub.2S"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/22 12:36
S5	0	(@ad<"20020820" or @rlad<"20020820") and ((ferroelectric adj memory) or FRAM or (ferroelectric adj device)) and schottky and (FET or (field adj effect adj transistor) or MOSFET) and "Ag" and "Pt" and "Cu" and "Cu.sub.2S"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/22 12:36
S4	0	(@ad<"20020820" or @rlad<"20020820") and ((ferroelectric adj memory) or FRAM or (ferroelectric adj device)) and schottky and (FET or (field adj effect adj transistor) or MOSFET) and chalcogenide and "Ag" and "Pt" and "Cu" and "Cu.sub.2S"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/22 12:35

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S2	2	"20050269611"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/22 12:27
S1	0	"10050269611"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/22 10:29